AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A semiconductor polishing composition eomprising consisting of:

fumed silica as abrasive grains, the fumed silica having a bulk density of 50 g/L or more and less than 100 g/L;

an acidic aqueous solution;

an alkali aqueous solution; and

coarse particles of 0.5 µm in diameter, the number of course particles being in a range of 66,595/0.5 ml to 112,453/0.5 mlno more than 140,000/0.5 ml, wherein the alkali aqueous solution contains at least one additive selected from a group consisting of a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant, wherein an average particle diameter of the particles of the fumed silica is in a range of 5 nm to 20 nm.

- 2. (Original) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.
 - 3.-6. (Cancelled)

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7. (Previously Presented) The semiconductor polishing composition of claim 1, wherein the alkali aqueous solution includes at least one hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

8. (Cancelled)

9. (Previously Presented) The semiconductor polishing composition of claim 2, wherein the alkali aqueous solution includes at least one hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

10.-11. (Cancelled)

<End of Claims Listing>